

TOSHIBA

2SC2884

TOSHIBA TRANSISTOR SILICON NPN EPITAXIAL TYPE (PCT PROCESS)

2SC2884

AUDIO FREQUENCY AMPLIFIER APPLICATIONS.

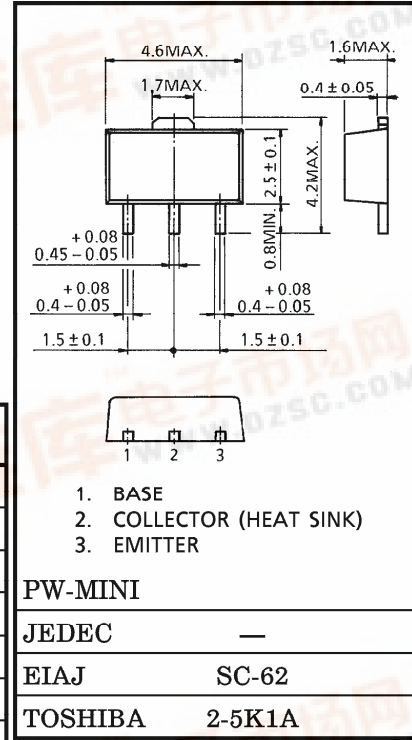
- High DC Current Gain : $h_{FE} = 100 \sim 320$
- Suitable for Output Stage of 1 Watts Amplifier
- $P_C = 1 \sim 2W$ (Mounted on Ceramic Substrate)
- Small Flat Package
- Complementary to 2SA1204

MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	35	V
Collector-Emitter Voltage	V_{CEO}	30	V
Emitter-Base Voltage	V_{EBO}	5	V
Collector Current	I_C	800	mA
Base Current	I_B	160	mA
Collector Power Dissipation	P_C	500	mW
Collector Power Dissipation	P_C (Note)	1000	mW
Junction Temperature	T_j	150	°C
Storage Temperature Range	T_{stg}	-55~150	°C

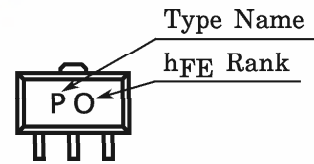
Note : Mounted on ceramic substrate (250mm²×0.8t)

Unit in mm



Weight : 0.05g

Marking



961001FAA2

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ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I_{CBO}	$V_{CB} = 35V, I_E = 0$	—	—	0.1	μA
Emitter Cut-off Current	I_{EBO}	$V_{EB} = 5V, I_C = 0$	—	—	0.1	μA
Collector-Emitter Breakdown Voltage	$V_{(BR) CEO}$	$I_C = 10mA, I_B = 0$	30	—	—	V
DC Current Gain	$h_{FE (1)}$ (Note)	$V_{CE} = 1V, I_C = 100mA$	100	—	320	
	$h_{FE (2)}$	$V_{CE} = 1V, I_C = 700mA$	35	—	—	
Collector-Emitter Saturation Voltage	$V_{CE (sat)}$	$I_C = 500mA, I_B = 20mA$	—	—	0.5	V
Base-Emitter Voltage	V_{BE}	$V_{CE} = 1V, I_C = 10mA$	0.5	—	0.8	V
Transition Frequency	f_T	$V_{CE} = 5V, I_C = 10mA$	—	120	—	MHz
Collector Output Capacitance	C_{ob}	$V_{CB} = 10V, I_E = 0, f = 1MHz$	—	13	—	pF

Note : $h_{FE (1)}$ Classification O : 100~200, Y : 160~320

